Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	1980	semiconductor and gate and source and drain and silicide and (silicid\$3 adj (gate or electrode))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/07 08:58
L2	867	semiconductor and (polysilicon adj (gate or electrode)) and source and drain and silicide and (silicid\$3 adj (gate or electrode))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/07 08:58
L3	867	semiconductor and (polysilicon adj (gate or electrode)) and source and drain and silicide and (silicid\$3 adj (gate or electrode))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/07 08:59
L4	739	semiconductor and (polysilicon adj (gate or electrode)) and source and drain and silicide and (silicid\$3 adj (gate or electrode)) and @ad<="20040326"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/07 09:09
L5	175	semiconductor and (polysilicon adj (gate or electrode)) and source and drain and silicide and (silicid\$3 adj (gate or electrode)) and @ad<="20040326" and polycide	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/07 09:10
S6	0	(polysilicon adj gate adj electrode) with (protect\$ adj (layer or film)) with (wet adj etch\$6)	US-PGPUB; USPAT	OR	ON	2006/09/07 08:56
S7	114	(polysilicon adj gate adj electrode) and (protect\$ adj (layer or film)) and (wet adj etch\$6)	US-PGPUB; USPAT	OR	ON	2005/06/07 08:54
S8	2	(polysilicon adj gate adj electrode) same (protect\$ adj (layer or film)) same (wet adj etch\$6)	US-PGPUB; USPAT	OR	ON	2005/06/07 09:10
S9	0	438/257,583.ccls. and(polysilicon adj gate adj electrode) same (protect\$ adj (layer or film)) same (wet adj etch\$6)	US-PGPUB; USPAT	OR	ON	2005/06/07 09:10
S10	0	438/257,583.ccls. and (polysilicon adj gate adj electrode) same (protect\$ adj (layer or film)) same (wet adj etch\$6)	US-PGPUB; USPAT	OR	ON	2006/09/07 08:57

S11	2	438/257,583.ccls. and (polysilicon adj gate adj electrode) and (protect\$ adj (layer or film)) and (wet adj etch\$6)	US-PGPUB; USPAT	OR	ON	2005/06/07 09:10
S12	2	(polysilicon adj gate adj electrode) with (source and drain) with ((protect\$ or block\$6) adj (layer or film)) with (silicide)	US-PGPUB; USPAT	OR	ON	2005/06/08 10:38
S13	213	(polysilicon adj gate adj electrode) and (source and drain) and ((protect\$ or block\$6) adj (layer or film)) and (silicide)	US-PGPUB; USPAT	OR	ON	2005/06/08 10:50
S18	39	(polysilicon adj gate adj electrode) and (source and drain) and (((protect\$ or block\$6) adj (layer or film)) with (silicide))	US-PGPUB; USPAT	OR	ON	2005/06/08 10:50
S19	13	(polysilicon adj gate adj electrode) and (source and drain) and (((protect\$ or block\$6) adj (layer or film)) near (silicide))	US-PGPUB; USPAT	OR	ON	2005/06/08 10:59
S20	76	(polysilicon adj gate adj electrode) and (source and drain) and (((protect\$ or block\$6) adj (layer or film)) same (silicide))	US-PGPUB; USPAT	OR	ON	2005/06/08 10:50
S21	134	(polysilicon adj gate adj electrode) and (source and drain) and (((protect\$ or block\$6 or mask\$6) adj (layer or film)) same (silicide))	US-PGPUB; USPAT	OR	ON	2005/06/08 10:51
S22	75	(polysilicon adj gate adj electrode) and (source and drain) and (((protect\$ or block\$6 or mask\$6) adj (layer or film)) with (silicide))	US-PGPUB; USPAT	OR	ON	2005/06/08 11:06
S23	55	(polysilicon adj gate adj electrode) and (source and drain) and (((protect\$ or block\$6 or masking) adj (layer or film)) with (silicide))	US-PGPUB; USPAT	OR	ON	2005/06/08 11:03
S24	75	(polysilicon adj gate adj electrode) and (source and drain) and (((protect\$ or block\$6 or mask\$6) adj (layer or film)) with (silicide)) and @ad<="20040326"	US-PGPUB; USPAT	OR	ON	2005/11/17 13:35
S25	8	(("6800905") or ("6770516") or ("6768158") or ("6630388") or ("6525403") or ("6432829") or ("6642090") or ("6764884")).PN.	USPAT	OR	OFF	2005/06/08 13:33

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S27	75	(polysilicon adj gate adj electrode) and (source and drain) and ((((protect\$ or block\$6 or mask\$6) adj (layer or film)) with (silicide)) with (silicid\$6)) and @ad<="20040326"	US-PGPUB; USPAT	OR ·	ON	2005/06/08 12:26
S28	8	((polysilicon adj gate adj electrode) same (source and drain) same ((((protect\$ or block\$6 or mask\$6) adj (layer or film)) with (silicide)) with (silicid\$6))) and @ad<="20040326"	US-PGPUB; USPAT	OR	ON	2005/06/08 12:27
S29	2	((polysilicon adj gate adj electrode) with (source and drain) with ((((protect\$ or block\$6 or mask\$6) adj (layer or film)) with (silicide)) with (silicid\$6))) and @ad<="20040326"	US-PGPUB; USPAT	OR	ON	2005/06/10 07:12
S30.	75	((polysilicon ad) gate adj electrode) and (source and drain) and ((((protect\$ or block\$6 or mask\$6) adj (layer or film)) with (silicide)) with (silicid\$6))) and @ad<="20040326"	US-PGPUB; USPAT	OR	ON	2005/06/08 12:27
S31	2	((polysilicon adj gate adj electrode) with (source and drain) with ((((protect\$ or block\$6 or mask\$6) adj (layer or film)) with (silicide)) with (silicid\$6 or salicid\$6))) and @ad<="20040326"	US-PGPUB; USPAT	OR	ON	2005/06/08 12:29
S32	8	((polysilicon adj gate adj electrode) same (source and drain) same ((((protect\$ or block\$6 or mask\$6) adj (layer or film)) with (silicide)) with (silicid\$6 or salicid\$6))) and @ad<="20040326"	US-PGPUB; USPAT	OR	ON	2005/06/08 12:29
S33	16	(("6787854") or ("6642090") or ("6475890") or ("6472258") or ("6475869") or ("20020153587") or ("20020130354") or ("20020177263") or ("20030122186") or ("6583469") or ("6413802") or ("6458662") or ("6300182") or ("5757038")).PN.	US-PGPUB; USPAT	OR	OFF	2005/06/08 14:05

S34	7	(("5462638") or ("5486282") or ("5796168") or ("5620611") or ("5937320") or ("6293457") or ("6468413")).PN.	US-PGPUB; USPAT	OR	OFF	2005/06/08 14:56
S94	1	("6489229").PN.	USPAT	OR	OFF	2005/06/10 07:24
S10 1	7	(("20050121748") or ("5323032") or ("5665616") or ("5599723")). PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/10 06:51
S10 3	2	(((polysilicon adj gate adj electrode) and (source and drain)) with (((protect\$ or block\$6 or mask\$6) adj (layer or film)) with (silicide)) with (silicid\$6 or salicid\$6)) and @ad<="20040326"	US-PGPUB; USPAT	OR	ON	2005/06/10 07:16
S10 4	15	(((polysilicon adj gate adj electrode) and (source and drain)) with ((silicid\$6 or salicid\$6) adj gate)) and @ad<="20040326"	US-PGPUB; USPAT	OR	ON	2005/06/10 07:21
S10 5	99	(438/583).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/10 07:22
S10 6	1232	(438/592).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/10 07:23
S10 7	485	(438/649).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/10 07:23
S10 8	132	(438/651).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/10 07:23
S10 9	1	("6140210").PN.	USPAT	OR	OFF	2005/06/10 07:24

S11 0	1	("20050215037").PN.	US-PGPUB	OR	OFF	2005/11/03 14:34
S11 1	7113	((gate or electrode) with (silicid\$4 or salicid\$4)) and ((source and drain) with (silicide))	US-PGPUB; USPAT	OR	ON	2005/11/03 14:37
S11 2	6910	((gate) with (silicid\$4 or salicid\$4)) and ((source and drain) with (silicide))	US-PGPUB; USPAT	OR	ON	2005/11/03 14:37
S11 3	6889	((gate) with (silicid\$4 or salicid\$4)) and ((source same drain) with (silicide))	US-PGPUB; USPAT	OR	ON	2005/11/03 14:37
S11 4	6185	((gate) with (silicid\$4 or salicid\$4)) and ((source near drain) with (silicide))	US-PGPUB; USPAT	OR	ON	2005/11/03 14:38
S11 5	4891	(((gate) with (silicid\$4 or salicid\$4)) and ((source near drain) with (silicide))) and polysilicon	US-PGPUB; USPAT	OR	ON	2005/11/03 14:41
S11 6	849	(((gate) with (silicid\$4 or salicid\$4)) and ((source near drain) with (silicide))) and (silicid\$4 adj gate)	US-PGPUB; USPAT	OR	ON	2005/11/04 08:58
S11 7	592	(((gate) with (silicid\$4 or salicid\$4)) and ((source near drain) with (silicide))) and (silicid\$4 adj gate)	USPAT	OR	ON	2005/11/04 08:32
S11 8	257	(((gate) with (silicid\$4 or salicid\$4)) and ((source near drain) with (silicide))) and (silicid\$4 adj gate)	US-PGPUB	OR	ON	2005/11/04 08:58
S12 1	6	(("6821887") or ("6555453") or ("6096609")).PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/17 13:20
S12 2	9	(polysilicon adj gate adj electrode) and (source and drain) and (((protect\$ or block\$6 or mask\$6) adj (layer or film)) with (silicide)) and @ad<="20040326" and (cobalt adj silicide) and (nickel adj silicide)	US-PGPUB; USPAT	OR	ON	2006/05/02 18:50

S12 8	4	(polysilicon adj gate) and (source and drain) and (((protect\$ or block\$6 or mask\$6) adj (layer or film)) near (silicide)) and (silicid\$4 or salicid\$4) and @ad<="20040326" and (cobalt adj silicide) and (nickel adj silicide)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/02 18:56
S12 9	208	(polysilicon adj gate) and (source and drain) and (silicide adj (layer or film)) and (silicid\$4 or salicid\$4) and @ad<="20040326" and (cobalt adj silicide) and (nickel adj silicide)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/03 10:20
S13 1	2585	(gate or (gate adj electrode)) near silicide	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/03 10:19
S13 2	2306	(gate) near silicide	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/03 10:19
S13 3	26	(polysilicon adj gate) and (source and drain) and (silicide adj (layer or film)) and ((silicid\$4 or salicid\$4) adj (polysilicon adj gate)) and @ad<="20040326" and (cobalt adj silicide) and (nickel adj silicide)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/03 10:21
S13 4	165	(polysilicon adj gate) and (source and drain) and (silicide adj (layer or film)) and ((silicid\$4 or salicid\$4) adj (polysilicon adj gate)) and @ad<="20040326"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/03 10:21
S13 5	2	(("6514859") or ("6562718")).PN.	USPAT	OR	OFF	2006/05/11 08:43
S13 6	4	(("20050215055") or ("6,864, 178") or ("6,620,718") or ("6,830, 987")).PN.	US-PGPUB; USPAT	OR	OFF	2006/05/11 09:45
S13 7	6	(("20050215055") or ("6,864, 178") or ("6,620,718") or ("6,830, 987") or ("6514859") or ("6562718")).PN.	US-PGPUB; USPAT	OR	OFF	2006/05/11 09:45